

AMENDMENTS TO THE CLAIMS

1-7. (Cancelled)

8. (Currently Amended) An ESD protection component, comprising:
at least two MOS field effect transistors (FETs) of a first conductivity type,
having two gates and formed in parallel on a first semiconductive layer having a
second conductivity type; and
a first well having a first conductivity type, formed on the first
semiconductive layer, comprising:
a connecting area, formed between the MOS FETs;
two parallel extension areas, formed perpendicular to the gates of the FETs;
and
a first doping area of the second conductivity type, formed in the connecting
area;
wherein each of the MOS FETs has a drain region of the first conductivity
type, and the drain regions of the MOS FETs are commonly and directly connected
to a single pad.

9. (Cancelled)

10. (Previously Presented) The ESD protection component as claimed in claim 8, wherein the first doping area is directly connected to the pad.

11. (Currently Amended) The ESD protection component as claimed in claim 8, wherein each of the MOS FETs has a source region of the first conductivity type, and the source regions of the MOS FETs are commonly and directly connected to a power rail.

12. (Previously Presented) The ESD protection component as claimed in claim 8, wherein the first well is electrically connected to the pad through the extension areas.